METHOD OF PRODUCING BONDED WAFER

ABSTRACT OF THE DISCLOSURE

A method of producing a bonded wafer, comprising: performing bonding of a first semiconductor wafer and a second semiconductor wafer without interposing an insulation film in between; and performing thinning of the second semiconductor wafer, wherein surface portions at least including bonded surfaces of the first semiconductor wafer and the second semiconductor wafer have an oxygen concentration of 1.0×10^{18}atoms/cm^3 (Old ASTM) or less.

Figure 1